

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 7,023,739 B2
APPLICATION NO. : 10/729844
DATED : April 4, 2006
INVENTOR(S) : En-Hsing Chen et al.

Page 1 of 1

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Column 22:

Line 43, the words "programmed stated" should read -- programmed state --.

Column 23:

Line 4, the word "suicide" should read -- silicide --.

Column 27:

Line 1, the words "A 2556 kb 3.0V ITIMTJ" should read -- A 256 kb 3.0V 1M1MTJ --.

Column 28:

Line 47, the word "use" should read -- used --.

Column 36:

Line 18, the word "NAND)" should read -- NAND --.

Signed and Sealed this

Eighth Day of August, 2006



JON W. DUDAS
Director of the United States Patent and Trademark Office